

MMBD4448W SWITCHING DIODE

FEATURES

Power dissipation

P_D : 200 mW ($T_{amb}=25^{\circ}C$)

Collector current

I_O : 250 mA

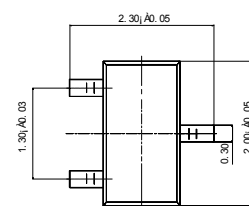
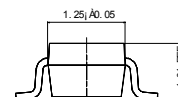
Collector-base voltage

V_R : 75 V

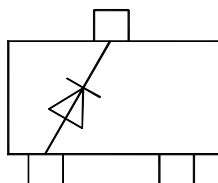
Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-323



Unit: mm



Marking: KA3

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R = 10\mu A$	75		V
Reverse voltage leakage current	I_R	$V_R = 20V$ $V_R = 75V$		0.025 2.5	μA
Forward voltage	V_F	$I_F = 5mA$ $I_F = 10mA$ $I_F = 100mA$ $I_F = 150mA$		0.72 0.855 1 1.25	V
Diode capacitance	C_D	$V_R = 0V, f = 1MHz$		4	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 10mA$ $I_{rr} = 0.1 \times I_R, R_L = 100\Omega$		4	nS

Test period $< 3000\mu s$.